

BLF6G20-230PRN

Power LDMOS transistor

Rev. 01 — 2 December 2008

Objective data sheet

1. Product profile

1.1 General description

230 W LDMOS power transistor for base station applications at frequencies from 1800 MHz to 2000 MHz.

Table 1. Typical performance

RF performance at $T_{case} = 25\text{ }^{\circ}\text{C}$ in a common source class-AB production test circuit.

Mode of operation	f (MHz)	V_{DS} (V)	$P_{L(AV)}$ (W)	G_p (dB)	η_D (%)	ACPR (dBc)
2-carrier W-CDMA	1805 to 1880	28	50	16.5	29.5	-35 ^[1]

[1] Test signal: 3GPP; test model 1; 64 DPCH; PAR = 7.5 dB at 0.01 % probability on CCDF per carrier; carrier spacing 5 MHz.

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features

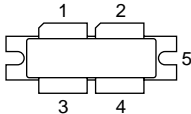
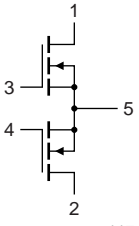
- Typical 2-carrier W-CDMA performance at frequencies of 1805 MHz and 1880 MHz, a supply voltage of 28 V and an I_{DQ} of 2000 mA:
 - ◆ Average output power = 50 W
 - ◆ Power gain = 16.5 dB (typ)
 - ◆ Efficiency = 29.5 %
 - ◆ ACPR = -35 dBc
- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (1800 MHz to 2000 MHz)
- Internally matched for ease of use
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- RF power amplifiers for W-CDMA base stations and multi carrier applications in the 1800 MHz to 2000 MHz frequency range

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	drain1		 sym117
2	drain2		
3	gate1		
4	gate2		
5	source		

[1] Connected to flange

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF6G20-230PRN	-	flanged balanced LDMOST ceramic package; 2 mounting holes; 4 leads	SOT539A

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
T_{stg}	storage temperature		-65	+150	°C
T_{case}	case temperature		-	150	°C
T_j	junction temperature		-	225	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-case)}$	thermal resistance from junction to case	$T_{case} = 80\text{ °C}$; $P_{L(AV)} = 50\text{ W}$	0.38	K/W

6. Characteristics

Table 6. Characteristics

$T_j = 25\text{ °C}$ per section; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0\text{ V}$; $I_D = 0.5\text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10\text{ V}$; $I_D = 144\text{ mA}$	1.575	1.9	2.3	V
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 32\text{ V}$; $I_D = 800\text{ mA}$	1.725	2.1	2.45	V
I_{DSS}	drain leakage current	$V_{GS} = 0\text{ V}$				
		$V_{DS} = 28\text{ V}$	-	-	3	μA
		$V_{DS} = 60\text{ V}$	-	-	5	μA
I_{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75\text{ V}$; $V_{DS} = 10\text{ V}$	-	25	-	A
I_{GSS}	gate leakage current	$V_{GS} = 11\text{ V}$; $V_{DS} = 0\text{ V}$	-	-	300	nA
g_{fs}	forward transconductance	$V_{DS} = 10\text{ V}$; $I_D = 7.2\text{ A}$	-	10	-	S
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75\text{ V}$; $I_D = 5\text{ A}$	-	0.1	0.165	Ω

7. Application information

Table 7. Application information

Mode of operation: 2-carrier W-CDMA; PAR 7.5 dB at 0.01 % probability on CCDF; 3GPP test model 1; 1 to 64 PDPCH; $f_1 = 1802.5\text{ MHz}$; $f_2 = 1807.5\text{ MHz}$; $f_3 = 1872.5\text{ MHz}$; $f_4 = 1877.5\text{ MHz}$; RF performance at $V_{DS} = 28\text{ V}$; $I_{Dq} = 2000\text{ mA}$; $T_{case} = 25\text{ °C}$; unless otherwise specified; in a class-AB production test circuit

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G_p	power gain	$P_{L(AV)} = 50\text{ W}$	<td>	16.5	<td>	dB
RL_{in}	input return loss	$P_{L(AV)} = 50\text{ W}$	-	-10	<td>	dB
η_D	drain efficiency	$P_{L(AV)} = 50\text{ W}$	<td>	29.5	-	%
ACPR	adjacent channel power ratio	$P_{L(AV)} = 50\text{ W}$	-	-35	<td>	dBc

Table 8. Application information

Mode of operation: 1-carrier W-CDMA; PAR 7.5 dB at 0.01 % probability on CCDF; 3GPP test model 1; 1 to 64 PDPCH; $f_1 = 1872.5\text{ MHz}$; $f_2 = 1877.5\text{ MHz}$; RF performance at $V_{DS} = 28\text{ V}$; $I_{Dq} = 2000\text{ mA}$; $T_{case} = 25\text{ °C}$; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
PAR_O	output peak-to-average ratio	$P_{L(AV)} = 115\text{ W}$; at 0.01 % probability on CCDF	-	4.3	-	dB

8. Package outline

Flanged balanced LDMOST ceramic package; 2 mounting holes; 4 leads

SOT539A

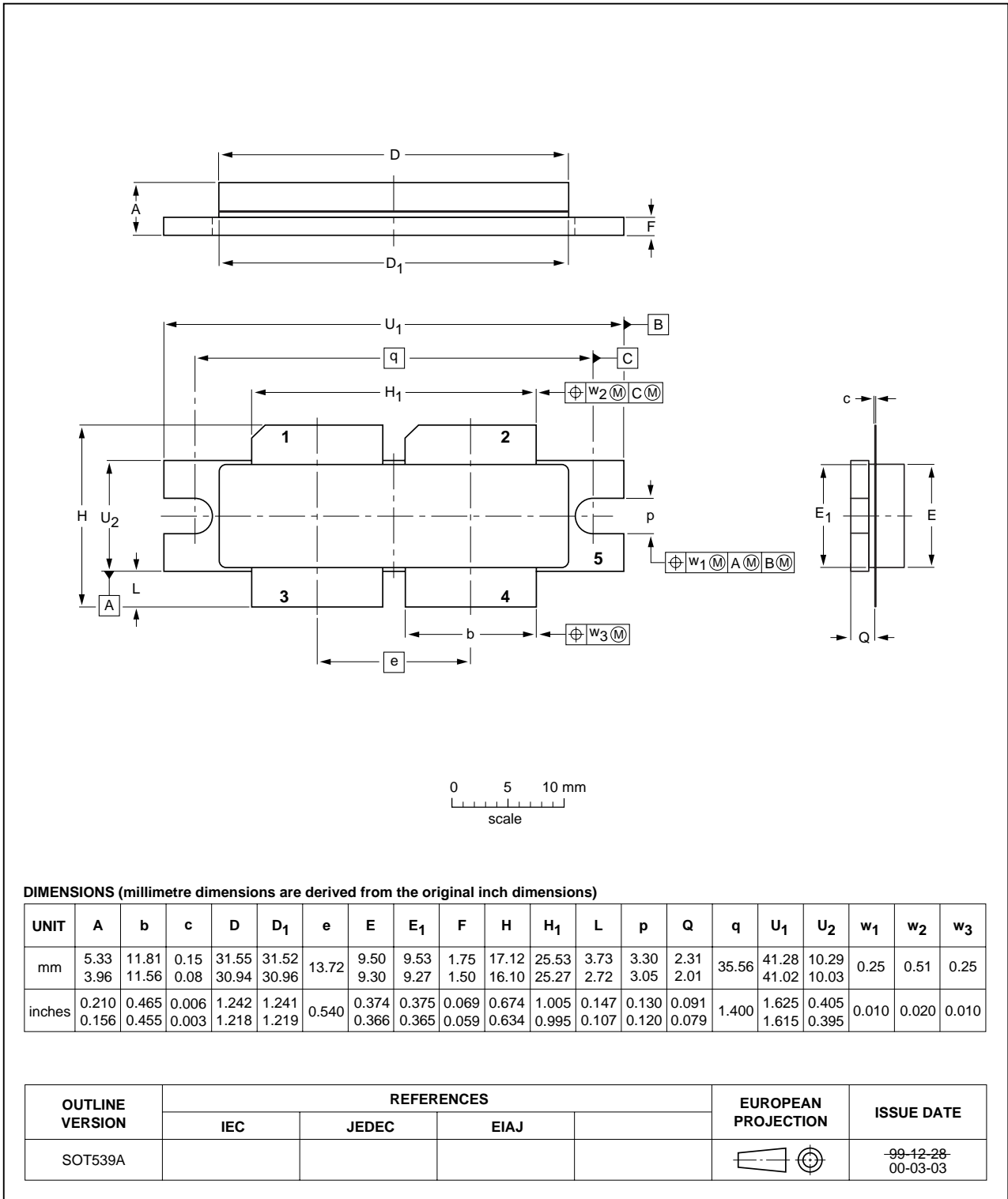


Fig 1. Package outline SOT539A

9. Abbreviations

Table 9. Abbreviations

Acronym	Description
3GPP	Third Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
DPCH	Dedicated Physical CHannel
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LDMOST	Laterally Diffused Metal-Oxide Semiconductor Transistor
PAR	Peak-to-Average power Ratio
PDPCH	transmission Power of the Dedicated Physical CHannel
RF	Radio Frequency
W-CDMA	Wideband Code Division Multiple Access

10. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF6G20-230PRN_1	20081202	Objective data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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